

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

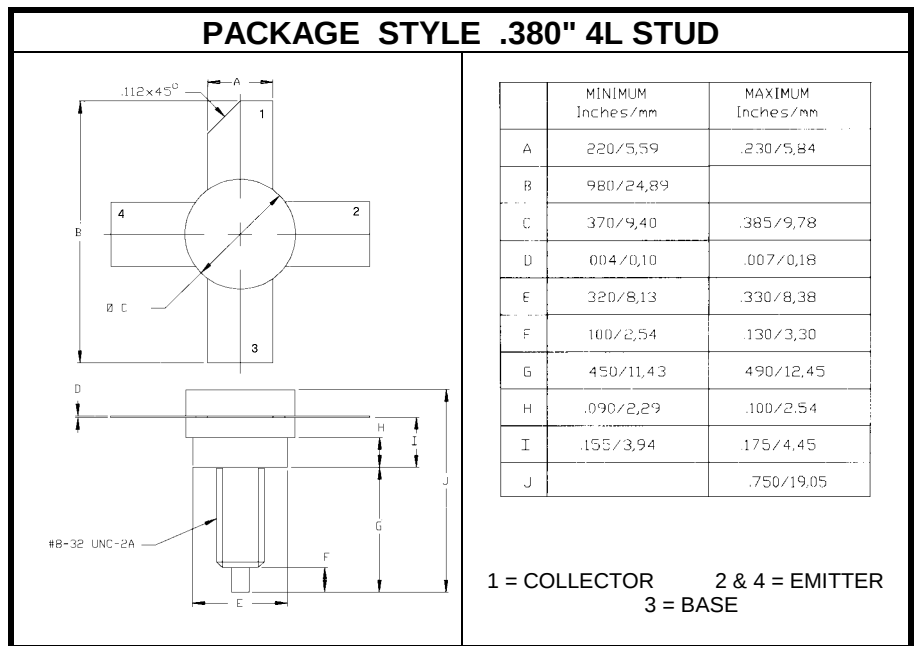
The **ASI BLY91C** is Designed for
28 V Large Signal Class A,B and C
Amplifier Applications up to 175 MHz.

FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- 3/8" SOE Stud Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	35 V
V_{CB}	65 V
P_{DISS}	20 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	8.7°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200\text{ mA}$	65			V
BV_{CEO}	$I_C = 10\text{ mA}$	35			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 36\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 400\text{ mA}$	10		100	---
C_{OB}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			15	pF
P_G	$V_{CC} = 28\text{ V}$ $P_{OUT} = 8.0\text{ W}$ $f = 175\text{ MHz}$	12.0	13.0		dB
η_C		65			%